

*SPECIFICATION AMENDMENTS*

Replace the paragraph beginning at page 1, line 7 with:

This invention relates to packages for ~~Optical~~ optical semiconductor devices, especially a package for ~~Optical~~ optical semiconductor devices that are excellent in high frequency characteristics.

Replace the paragraph beginning at page 1, line 23 with:

The conventional stem type package ~~is constituted as follows by using the~~ includes a stem-body 113, as shown in Fig. 9A and Fig. 9B. ~~Pair~~ A pair of lead terminals 105 for photodiodes and a lead terminal 112 for signal supply are inserted in ~~the~~ the respective through holes of stem-body 113 ~~respectively so as to be~~ and insulated by a glass 106. Moreover, a sub-mount 102 and a mount 901, in which a semiconductor laser 103 is mounted ~~are~~ are arranged, adjoins the lead terminal 112 for signal supply on the upper surface of the stem-body 113, and a recess 109, in which sub-mount 108 and the photodiode 107 for ~~monitor~~ monitoring are attached ~~formed, is located~~ is located at the upper surface of stem-body 113. Here, the recess 109 is ~~formed in a position located~~ located where the laser light from the monitor ~~side edge~~ edge face, opposite to light emitting ~~edge~~ edge face of the semiconductor laser diode, is ~~inputted~~ input into the photodiode 107 for ~~monitors~~ monitoring, mounted on sub-mount 108. In addition, an earth lead terminal 114 is attached ~~and shown with the code of 114~~ as in Fig. 9A.

Replace the paragraph beginning at page 2, line 24 with:

In the semiconductor laser device formed as mentioned above, when a voltage of about 1.5V is applied between the lead terminal for signal supply 112 and the earth lead terminal 114, an electrical current of tens of mA ~~is flowed~~ flows in the semiconductor laser device and a laser light is emitted. ~~And a~~ The light emitted from the ~~edge~~ edge face opposite to the light emitting face is ~~received~~ detected at the monitor photodiode 107 to control the quantity of the emitted light.

Replace the paragraph beginning at page 3, line 7 with:

~~In the stem-type Stem~~ Stem packages for optical semiconductor device, ~~the structures~~ with good heat radiating properties ~~capable of~~ for radiating the heat generated by the

semiconductor laser devices, are shown in ~~the documents of~~ Japanese Non-examined Patent Publications No.58-98995, No.07-240565 and U.S.Patent No.5,262,675.

Replace the paragraph beginning at page 3, line 13 with:

However, in the conventional package for ~~Optical~~ an optical semiconductor device, although the high frequency characteristics of a butterfly ~~type~~ package are good, it is made very expensive by the complicated structure. On the other hand, although the stem ~~type~~ package is cheap, high frequency characteristics are not good, so it is difficult to ~~be used~~ use for high-speed transmission ~~of~~ at 10Gbps or more.

Replace the paragraph beginning at page 7, line 7 with:

Fig. 12 is a cross sectional view taken along the line ~~A-B~~ XII-XII of Fig. 11B.

Replace the paragraph beginning at page 8, line 2 with:

Fig. 17 is a cross sectional view taken along the line ~~A-B~~ XVII-XVII of Fig. 16B.

Replace the paragraph beginning at page 8, line 25 with:

Fig. 23 is a cross sectional view taken along the line ~~A-B~~ XXIII-XXIII of Fig. 22B.

Replace the paragraph beginning at page 25, line 13 with:

Fig. 11A is a perspective view of the optical semiconductor device of Embodiment 6, and Fig. 11B is the top view thereof. Fig. 12 is a cross sectional view taken along the line ~~A-B~~ XII-XII of Fig. 11B.

Replace the paragraph beginning at page 30, line 9 with:

Fig. 16A is a perspective view of the optical semiconductor device of Embodiment 8, and Fig. 16B is the top view thereof. Fig. 17 is a cross sectional view taken along the line ~~A-B~~ XVII-XVII shown in Fig. 16B.